

Fig. 7 Typ. switching times vs. I_C

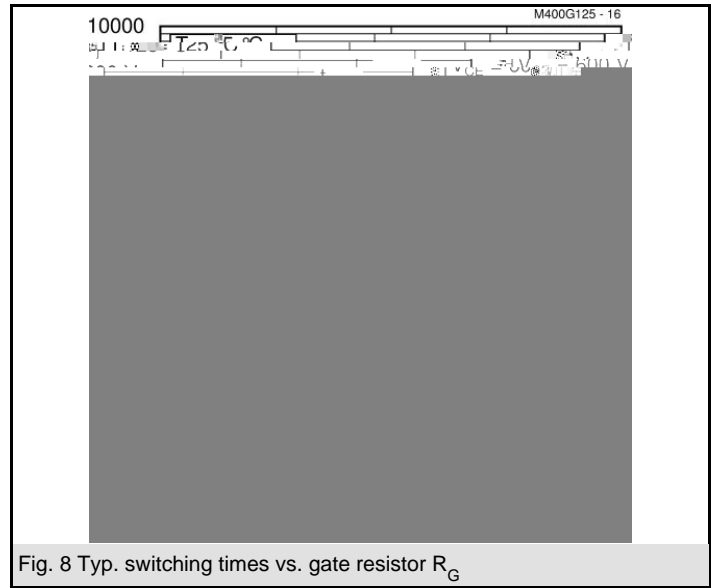


Fig. 8 Typ. switching times vs. gate resistor R_G

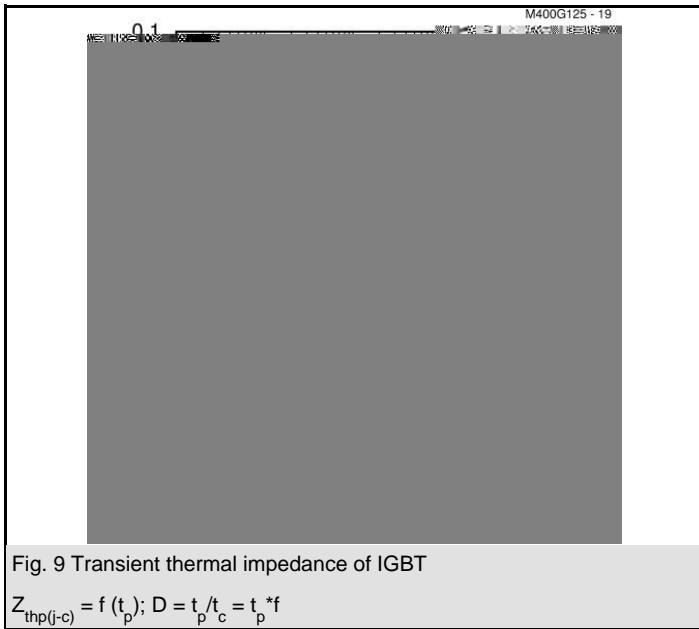


Fig. 9 Transient thermal impedance of IGBT

$$Z_{thp(j-c)} = f(t_p); D = t_p/t_c = t_p * f$$

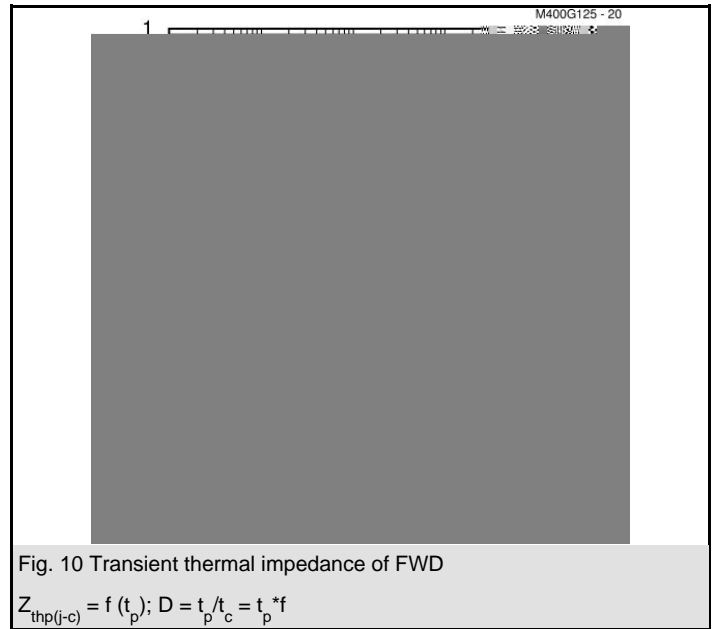


Fig. 10 Transient thermal impedance of FWD

$$Z_{thp(j-c)} = f(t_p); D = t_p/t_c = t_p * f$$

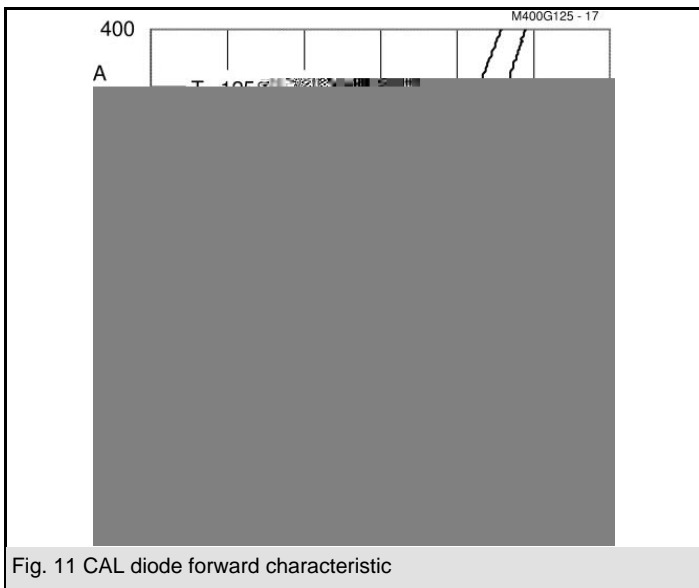


Fig. 11 CAL diode forward characteristic

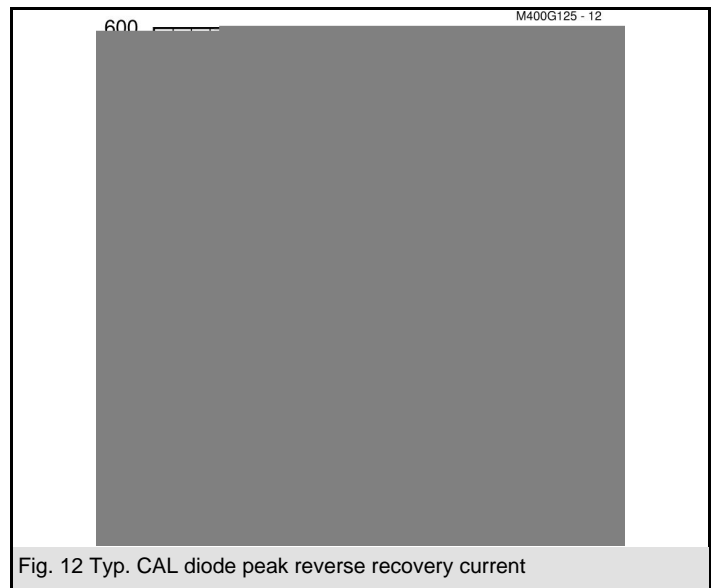


Fig. 12 Typ. CAL diode peak reverse recovery current

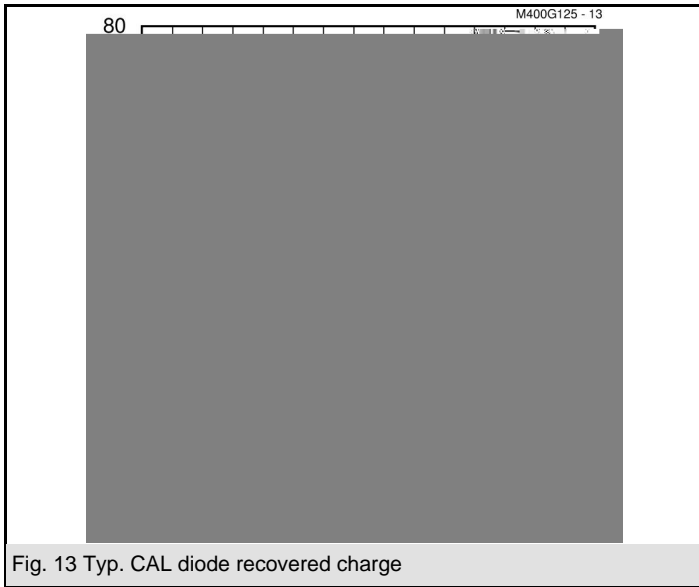
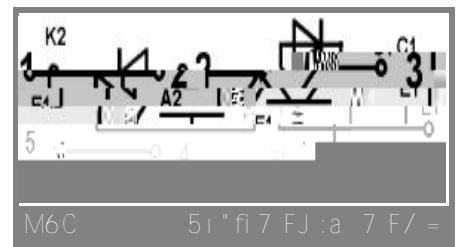
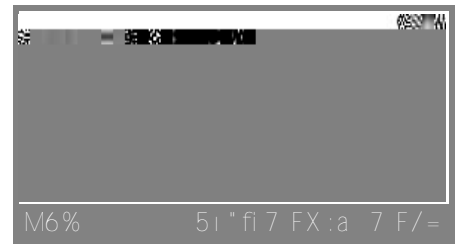
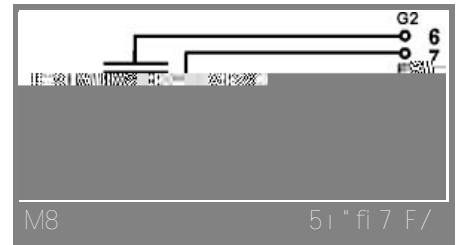


Fig. 13 Typ. CAL diode recovered charge

UL Recognized
File no. E 63 532

Dimensions in mm



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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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